Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I_{GT}	V_D =12V R_L =33	ƒ', õƒA, õA	GGT	

ORDERING INFORMATION

T 8 35 H -8 K -/

- T: Triacs
- 8: $I_{T(RMS)}$: 8A
- 35: I_{GT1-3} 035 mA
- H: High junction temperature
- -8: V_{DRM} /V_{RRM} 1800 V
- K: TO-252
- -/: Blank: Tube; -TR: Tape & Reel

MARKING Year

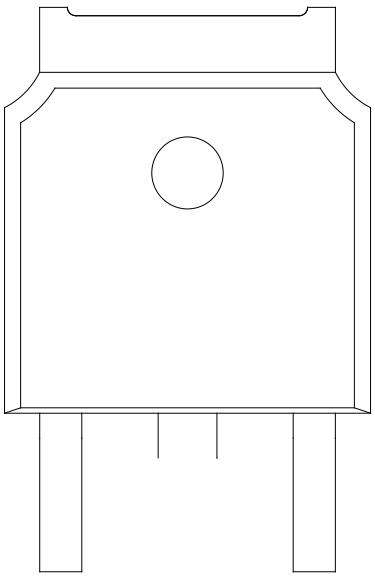


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

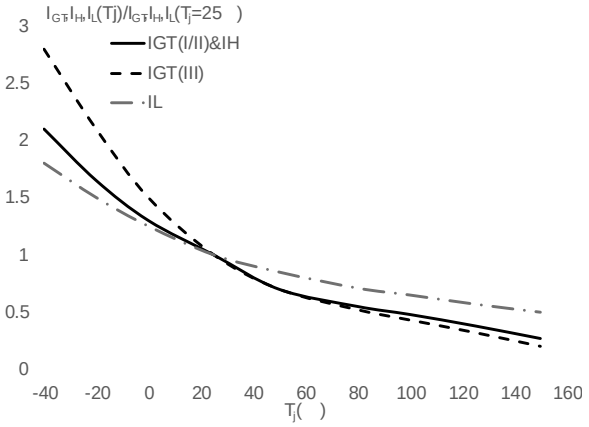
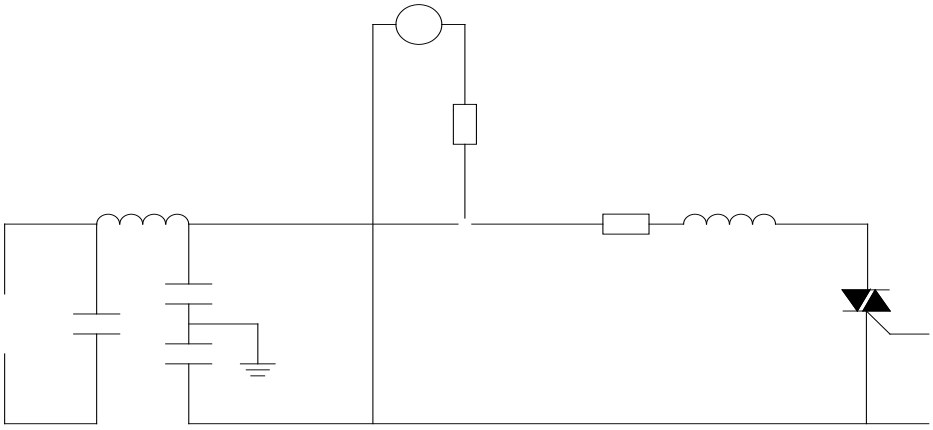


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



DELIVERY MODE



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